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DN2328 N-Channel Enhancement MOSFET

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Top View

SOT-23

General description

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

- V_{DS}=100V
- I_D=2A
- R_{DS(ON)}(at V_{GS}=10V)<310 mΩ
- $R_{DS(ON)}$ (at V_{GS}=4.5V)<350 m Ω
- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low R_{DS(ON)}

APPLICATIONS

- DC-DC Converters
- Power management functions

Device Marking:SA34

Absolute Maximum Ratings

Paramete		Symbol	Limit	Unit
Drain-source Voltage		V _{DS}	100	V
Gate-source Voltage		V _{GS}	±20	V
	T _A =25℃		2.0	
Drain Current	T _A =70℃	۱ _D	1.6	A
Pulsed Drain Current ^A	ulsed Drain Current ^A		8	A
Total Power Dissipation @ T _A =25℃		P _D	1.2	W
Thermal Resistance Junction-to-Ambient ^B		R _e JA	105	°C/ W
Junction and Storage Temperatu	re Range	Тյ ,Тѕтс	-55~+150	°C

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Electrical Characteristics

Parameter	Symbol	Conditions	Min	Тур	Мах	Units	
Static Parameter							
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V, I _D =250µA	100			V	
Zero Gate Voltage Drain Current	IDSS	V _{DS} =100V,V _{GS} =0V			1	μA	
Orthe Desite Landshare Ormanit	IGSS1	$V_{\text{GS}}\text{=}\pm20\text{V}, \text{V}_{\text{DS}}\text{=}0\text{V}$			±100	nA	
Gate-Body Leakage Current	IGSS2	$V_{\text{GS}}\text{=}\pm10\text{V}, V_{\text{DS}}\text{=}0\text{V}$			±50	nA	
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS} , I_D =250 μ A	1.1	1.8	3.0	V	
		V _{GS} = 10V, I _D =2.0A		240 310			
Static Drain-Source On-Resistance	Rds(on)	V _{GS} = 4.5V, I _D =2.0A		250	350	mΩ	
Diode Forward Voltage	V_{SD}	I _S =2A,V _{GS} =0V		0.8	1.2	V	
Maximum Body-Diode Continuous Current	ls				2.0	А	
Dynamic Parameters							
Input Capacitance	C _{iss}			330			
Output Capacitance	C _{oss}	V _{DS} =50V,V _{GS} =0V,f=1MHZ		88		pF	
Reverse Transfer Capacitance	C _{rss}			17			
Switching Parameters							
Total Gate Charge	Qg			5.3			
Gate-Source Charge	Q_{gs}	V_{GS} =10V, V_{DS} =50V, I_{D} =2.0A		1.4		nC	
Gate-Drain Charge	Q_{gd}			1.8			
Turn-on Delay Time	t _{D(on)}			14			
Turn-on Rise Time	tr	V _{GS} =10V,V _{DD} =50V,		54			
Turn-off Delay Time	t _{D(off)}	I _D =1.3A,R _L =39Ω R _{GEN} =1Ω		18		ns	
Turn-off fall Time	t _f			11			

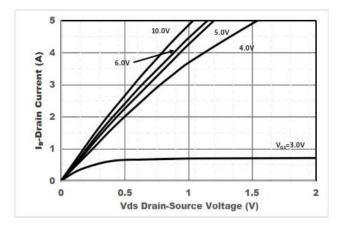
Note :

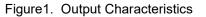
A. Pulse Test: Pulse Width \leq 300us, Duty cycle \leq 2%. B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch

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Typical Characteristics





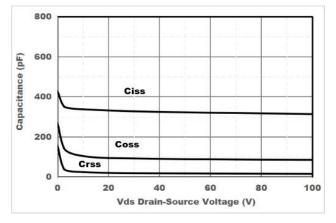


Figure3. Capacitance Characteristics

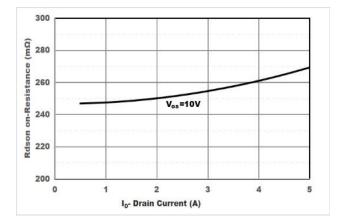
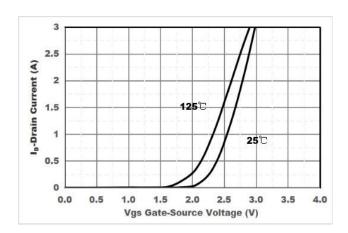
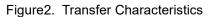
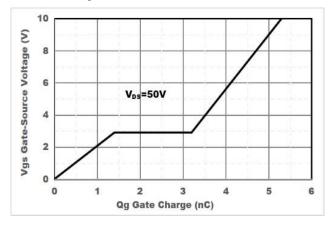


Figure5. Drain-Source on Resistance









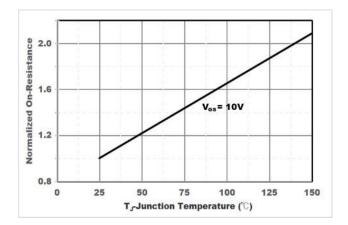
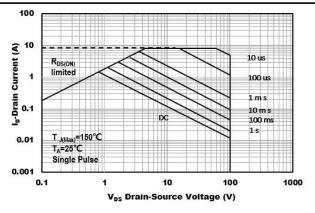


Figure6. Drain-Source on Resistance

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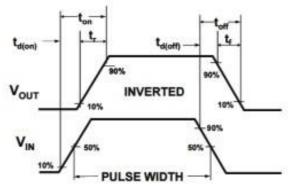
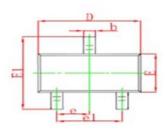
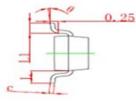


Figure7. Safe Operation Area



SOT-23 Package information

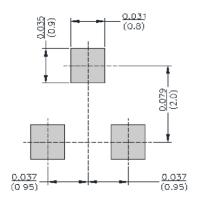




-		}	A2	-
		It		

Symbol	Dimentions in Millimeter		Dimentions in Inches	
	Min	Max	Min	Max
А	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
с	0.100	0.200	0.004	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
е	0.950Type		0.037Type	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.220REF	
L1	0.300	0.500	0.012	0.020
θ	0 °	8	0 °	8 °

SOT-23 Suggested Pad Layout





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